

Załącznik 2

Wykaz znaczących publikacji wnioskodawcy/ zespołu z pełnych ostatnich 3 lat.

1. K.Karpierz, J.Łusakowski, M.Szot, J.Kossut, M.Grynberg, *Potential fluctuations in CdTe epitaxial layers studied by shallow donor spectroscopy in the far infrared*, J.Phys.: Condens. Matter **20**, 2008, 195217. **24 p**
2. J. Łusakowski, K. J. Friedland, and K. Ploog, *The Stark effect on a bound hole in δ -acceptor doped GaAs/Al_xGa_{1-x}As heterostructures*, Solid State Comm. **142**, 299 (2007). **20 p**
3. J. Łusakowski, R. Buczko, M. Sakowicz, K. J. Friedland, R. Hey, and K. Ploog, *Interband spectroscopy to test the spherical acceptor model in δ -doped heterostructures*, J. Phys: Cond. Matt. **19**, 236205 (2007). **24 p**
4. J. Łusakowski, M. J. Martin Martinez, R. Rengel, T. Gonzalez, R. Tauk, Y. M. Meziani, W. Knap, F. Boeuf, and T. Skotnicki, *Quasi ballistic transport in nanometer Si metal-oxide-semiconductor field-effect transistors: experimental and Monte Carlo analysis*, J. Appl. Phys. **101**, 114511 (2007). **24 p**
5. J. Łusakowski, R. Buczko, M. Sakowicz, K. J. Friedland, R. Hey, and K. Ploog, *Spectroscopy of Be acceptor ground state in GaAs/AlGaAs heterostructure*, Acta Physica Polonica, Acta Physica Polonica **112 A**, 209 (2007). **10 p**
6. R.Tauk, J.Łusakowski, W.Knap, A.Tiberj, Z.Bougrioua, M.Azize, P.Lorenzini, M.Sakowicz, K.Karpierz, C.Fenouillet-Beranger, M. Casse, C.Gallon, F.Boeuf, T.Skotnicki, *Low electron mobility of field-effect transistor determined by modulated magnetoresistance*, J. Applied Physics **102**, 2007, 103701-103707. **24 p**
7. R.Tauk, A.Tiberj, P.Lorenzini, Z.Bougrioua, M.Azize, M.Sakowicz, K.Karpierz, W.Knap, *Magnetotransport characterization of AlGaN/GaN interfaces*, Phys. Stat. Solidi **A 204**, (2), 2007, 586-590. **20 p**
8. K.Karpierz, M.Szot and M.Grynberg, *Nonstandard absorption on Donors in Uniformly Doped II-VI 0D Structures*, Acta Physica Polonica **A 112**, 2007, 237-241. **10 p**
9. M.Sakowicz, J.Lusakowski, K.Karpierz, M.Grynberg, B.Majkusiak, *Transport and quantum scattering time in field-effect transistors*, Appl. Physics Lett.; **90** (17), 2007, 172104. **24 p**
10. M.Sakowicz, R.Tauk, J.Łusakowski, A.Tiberj, W.Knap, Z.Bougrioua, M.Azize, P.Lorenzini, K.Karpierz, M.Grynberg, *Low temperature electron mobility and concentration under the gate of AlGaN/GaN field effect transistors*, J.Applied Physics **100** (11), 2006, 113726. **24 p**
11. J. Łusakowski, W. Knap, Y. Meziani, J.- P. Cesso, A. el Fatimy, R. Tauk, N. Dyakonova, G. Ghibaudo, F. Boeuf and T. Skotnicki, *Electron mobility in quasi ballistic Si MOSFETs*, Solid State Electronics **50**, 632-636 (2006), **20 p**
12. N. Dyakonova, A. El Fatimy, J. Łusakowski, W. Knap, M. I. Dyakonov, M.-A. Poisson, E. Morvan, S. Bollaert, A. Shchepetov, Y. Roelens, Ch. Gaquiere, D. Theron,

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13. J. Łusakowski, F. Teppe, N. Dyakonova, Y. M. Meziani, W. Knap, T. Parenty, S. Bollaert, A. Cappy, V. Popov and M. S. Shur, *Terahertz generation by plasma waves in nanometer gate high electron mobility transistors*, Phys. Status Solidi (a) **202**, 656 (2005) **20 p**
14. W. Knap, J. Łusakowski, F. Teppe, N. Dyakonova, and Y. M. Meziani, *Terahertz generation and detection by plasma waves in nanometer gate high electron mobility transistors*, Proc. 12th Int. Symposium on Ultrafast Phenomena in Semiconductors, Vilnius 2004, Acta Physica Polonica **A 107**, 82 (2005) **10 p**
15. J. Łusakowski, W. Knap, N. Dyakonova, L. Varani, J. Mateos, T. Gonzalez, T. Parenty, S. Bollaret, A. Cappy and K. Karpierz, *Voltage tuneable terahertz emission from ballistic GaInAs/AlInAs transistor*, J. Appl. Phys. **97**, 064307 (2005) **24 p**
16. C. Skierbiszewski, W. Knap, M. Siekacz, K. Dybko, Z. Wasilewski, D. Maude, J. Łusakowski, W. Krupczyński, G. Nowak, M. Boćkowski, T. Suski and S. Porowski, *High mobility two-dimensional electron gas in AlGaN/GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy*, Appl. Phys. Lett. **86**, 102106-1-3 (2005) **24 p**
17. N. Dyakonova, F. Teppe, J. Łusakowski, W. Knap, M. Levinshstein, A. P. Dmitriev, M. S. Shur, S. Bollaert, and A. Cappy, *Magnetic field effect on the terahertz emission from nanometer InGaAs/AlInAs HEMTs*, J. Appl. Phys. **97**, 114313 (2005) **24 p**
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